



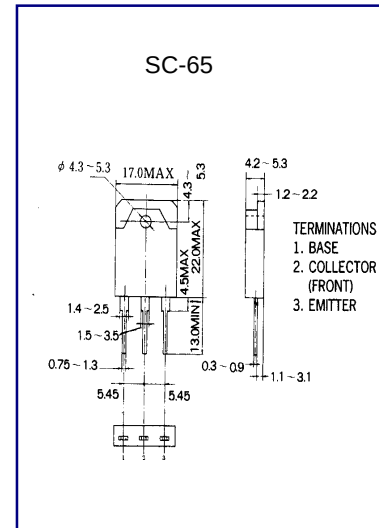
2SD1063

NPN PLANAR SILICON TRANSISTOR

- PSW / D / DDC
- COMPLEMENTARY TO 2SB827

ABSOLUTE MAXIMUM RATING ($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	60	V
Collector-Emitter Voltage	V_{CE0}	50	V
Emitter-Base voltage	V_{EB0}	6	V
Collector Current (DC)	I_C	7	A
Collector Dissipation	P_C	60	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV_{CB0}	$I_C=5\text{ mA}$ $I_E=0$	60			V
Collector Emitter Breakdown Voltage	BV_{CE0}	$I_C=10\text{ mA}$ $R_{BE}=\infty$	50			V
Emitter Base Breakdown Voltage	BV_{EB0}	$I_E=5\text{ mA}$ $I_C=0$	6			V
Collector Cutoff Current	I_{CB0}	$V_{CB}=60\text{ V}$ $I_E=0$			0.1	mA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=4\text{ V}$ $I_C=0$			0.1	mA
*DC Current Gain	H_{fe}	$V_{CE}=2\text{ V}$ $I_C=1\text{ A}$	70		280	
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4\text{ A}$ $I_B=0.4\text{ A}$			0.4	V